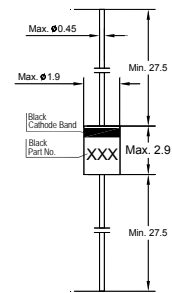


HZS...L Series

Silicon Epitaxial Planar Zener Diodes



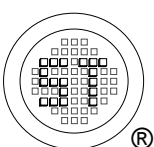
Glass Case DO-34
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Power Dissipation	P_{tot}	500	mW
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 175	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$ ($V_F = 1\text{ V Max. at } I_F = 100\text{ mA}$)

Type	Zener Voltage ¹⁾		Reverse Leakage Current		Dynamic Resistance		
	V_{ZT}		at I_{ZT} (mA)	I_R Max. (μA)	at V_R (V)	Z_{ZT} Max. (Ω)	at I_{ZT} (mA)
	Min. (V)	Max. (V)					
HZS6LA1	5.2	5.5	0.5	1	2	150	0.5
HZS6LA2	5.3	5.6	0.5	1	2	150	0.5
HZS6LA3	5.4	5.7	0.5	1	2	150	0.5
HZS6LB1	5.5	5.8	0.5	1	2	80	0.5
HZS6LB2	5.6	5.9	0.5	1	2	80	0.5
HZS6LB3	5.7	6	0.5	1	2	80	0.5
HZS6LC1	5.8	6.1	0.5	1	2	60	0.5
HZS6LC2	6	6.3	0.5	1	2	60	0.5
HZS6LC3	6.1	6.4	0.5	1	2	60	0.5
HZS7LA1	6.3	6.6	0.5	1	3.5	60	0.5
HZS7LA2	6.4	6.7	0.5	1	3.5	60	0.5
HZS7LA3	6.6	6.9	0.5	1	3.5	60	0.5
HZS7LB1	6.7	7	0.5	1	3.5	60	0.5
HZS7LB2	6.9	7.2	0.5	1	3.5	60	0.5
HZS7LB3	7	7.3	0.5	1	3.5	60	0.5
HZS7LC1	7.2	7.6	0.5	1	3.5	60	0.5
HZS7LC2	7.3	7.7	0.5	1	3.5	60	0.5
HZS7LC3	7.5	7.9	0.5	1	3.5	60	0.5
HZS9LA1	7.7	8.1	0.5	1	6	60	0.5
HZS9LA2	7.9	8.3	0.5	1	6	60	0.5
HZS9LA3	8.1	8.5	0.5	1	6	60	0.5
HZS9LB1	8.3	8.7	0.5	1	6	60	0.5
HZS9LB2	8.5	8.9	0.5	1	6	60	0.5
HZS9LB3	8.7	9.1	0.5	1	6	60	0.5
HZS9LC1	8.9	9.3	0.5	1	6	60	0.5
HZS9LC2	9.1	9.5	0.5	1	6	60	0.5
HZS9LC3	9.3	9.7	0.5	1	6	60	0.5
HZS11LA1	9.5	9.9	0.5	1	8	80	0.5
HZS11LA2	9.7	10.1	0.5	1	8	80	0.5



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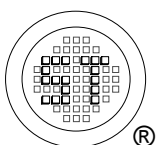


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Characteristics at $T_a = 25^\circ\text{C}$ ($V_F = 1\text{ V Max. at } I_F = 100\text{ mA}$)

Type	Zener Voltage ¹⁾			Reverse Leakage Current		Dynamic Resistance	
	V_{ZT}		at I_{ZT}	I_R	at V_R	Z_{ZT}	at I_{ZT}
	Min. (V)	Max. (V)	(mA)	Max. (μA)	(V)	Max. (Ω)	(mA)
HZS11LA3	9.9	10.3	0.5	1	8	80	0.5
HZS11LB1	10.2	10.6	0.5	1	8	80	0.5
HZS11LB2	10.4	10.8	0.5	1	8	80	0.5
HZS11LB3	10.7	11.1	0.5	1	8	80	0.5
HZS11LC1	10.9	11.3	0.5	1	8	80	0.5
HZS11LC2	11.1	11.6	0.5	1	8	80	0.5
HZS11LC3	11.4	11.9	0.5	1	8	80	0.5
HZS12LA1	11.6	12.1	0.5	1	10.5	80	0.5
HZS12LA2	11.9	12.4	0.5	1	10.5	80	0.5
HZS12LA3	12.2	12.7	0.5	1	10.5	80	0.5
HZS12LB1	12.4	12.9	0.5	1	10.5	80	0.5
HZS12LB2	12.6	13.1	0.5	1	10.5	80	0.5
HZS12LB3	12.9	13.4	0.5	1	10.5	80	0.5
HZS12LC1	13.2	13.7	0.5	1	10.5	80	0.5
HZS12LC2	13.5	14	0.5	1	10.5	80	0.5
HZS12LC3	13.8	14.3	0.5	1	10.5	80	0.5
HZS15L1	14.1	14.7	0.5	1	13	80	0.5
HZS15L2	14.5	15.1	0.5	1	13	80	0.5
HZS15L3	14.9	15.5	0.5	1	13	80	0.5
HZS16L1	15.3	15.9	0.5	1	14	80	0.5
HZS16L2	15.7	16.5	0.5	1	14	80	0.5
HZS16L3	16.3	17.1	0.5	1	14	80	0.5
HZS18L1	16.9	17.7	0.5	1	15	80	0.5
HZS18L2	17.5	18.3	0.5	1	15	80	0.5
HZS18L3	18.1	19	0.5	1	15	80	0.5
HZS20L1	18.8	19.7	0.5	1	18	100	0.5
HZS20L2	19.5	20.4	0.5	1	18	100	0.5
HZS20L3	20.2	21.1	0.5	1	18	100	0.5
HZS22L1	20.9	21.9	0.5	1	20	100	0.5
HZS22L2	21.6	22.6	0.5	1	20	100	0.5
HZS22L3	22.3	23.3	0.5	1	20	100	0.5
HZS24L1	22.9	24	0.5	1	22	120	0.5
HZS24L2	23.6	24.7	0.5	1	22	120	0.5
HZS24L3	24.3	25.5	0.5	1	22	120	0.5
HZS27L1	25.2	26.6	0.5	1	24	150	0.5
HZS27L2	26.2	27.6	0.5	1	24	150	0.5
HZS27L3	27.2	28.6	0.5	1	24	150	0.5
HZS30L1	28.2	29.6	0.5	1	27	200	0.5
HZS30L2	29.2	30.6	0.5	1	27	200	0.5
HZS30L3	30.2	31.6	0.5	1	27	200	0.5
HZS33L1	31.2	32.6	0.5	1	30	250	0.5
HZS33L2	32.2	33.6	0.5	1	30	250	0.5
HZS33L3	33.2	34.6	0.5	1	30	250	0.5
HZS36L1	34.2	35.7	0.5	1	33	300	0.5
HZS36L2	35.3	36.8	0.5	1	33	300	0.5
HZS36L3	36.4	38	0.5	1	33	300	0.5

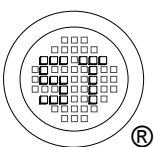
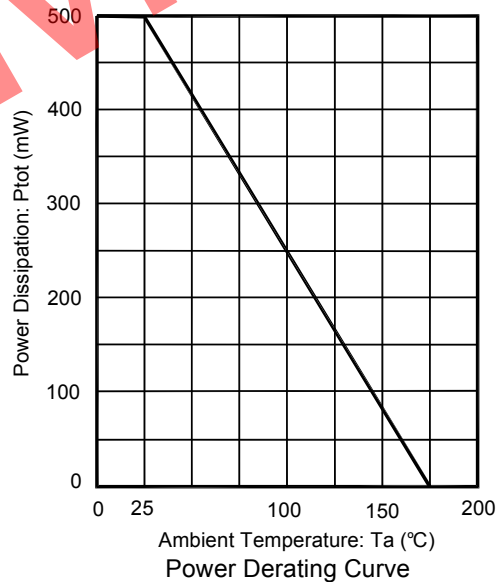
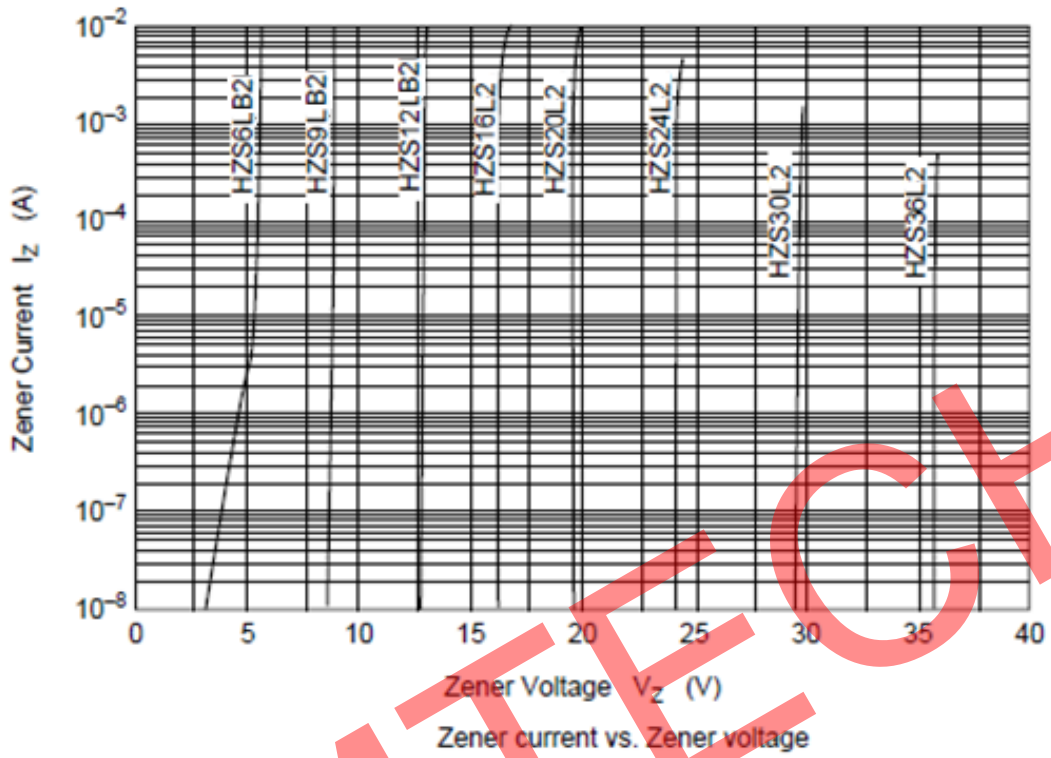
¹⁾ Tested with pulses $t_p = 20\text{ ms}$.



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